

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

# 2SA1244

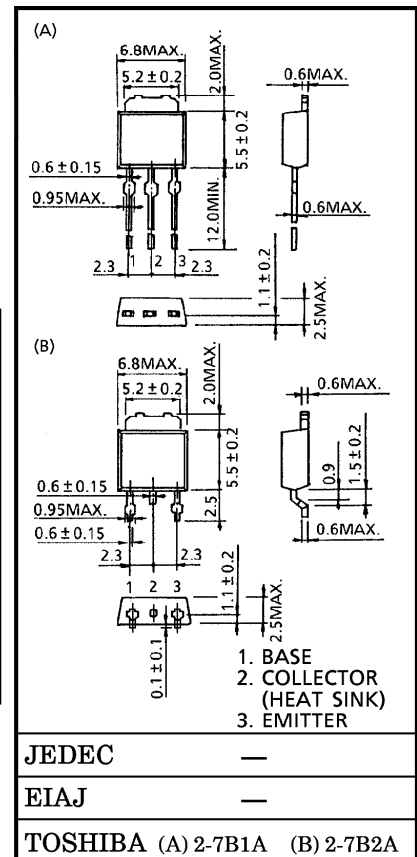
HIGH CURRENT SWITCHING APPLICATIONS

Unit in mm

- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = -0.4\text{ V (Max.) at } I_C = -3\text{ A}$
- High Speed Switching Time :  $t_{stg} = 1.0\ \mu\text{s (Typ.)}$
- Complementary to 2SC3074

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

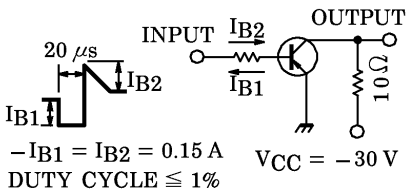
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		$V_{CBO}$	-60	V
Collector-Emitter Voltage		$V_{CEO}$	-50	V
Emitter-Base Voltage		$V_{EBO}$	-5	V
Collector Current		$I_C$	-5	A
Base Current		$I_B$	-1	A
Collector Power Dissipation	$T_a = 25^\circ\text{C}$	$P_C$	1.0	W
	$T_c = 25^\circ\text{C}$		20	
Junction Temperature		$T_j$	150	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		$I_{CBO}$	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-1	$\mu\text{A}$
Emitter Cut-off Current		$I_{EBO}$	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-1	$\mu\text{A}$
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-50	—	—	V
DC Current Gain		$h_{FE(1)}$ (Note)	$V_{CE} = -1\text{ V}, I_C = -1\text{ A}$	70	—	240	
		$h_{FE(2)}$	$V_{CE} = -1\text{ V}, I_C = -3\text{ A}$	30	—	—	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	$I_C = -3\text{ A}, I_B = -0.15\text{ A}$	—	-0.2	-0.4	V
	Base-Emitter	$V_{BE(sat)}$	$I_C = -3\text{ A}, I_B = -0.15\text{ A}$	—	-0.9	-1.2	
Transition Frequency		$f_T$	$V_{CE} = -4\text{ V}, I_C = -1\text{ A}$	—	60	—	MHz
Collector Output Capacitance		$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0,$ $f = 1\text{ MHz}$	—	170	—	pF
Switching Time	Turn-on Time	$t_{on}$	 <p><math>-I_{B1} = I_{B2} = 0.15\text{ A}</math> DUTY CYCLE <math>\leq 1\%</math> <math>V_{CC} = -30\text{ V}</math></p>	—	0.1	—	$\mu\text{s}$
	Storage Time	$t_{stg}$		—	1.0	—	
	Fall Time	$t_f$		—	0.1	—	

Note :  $h_{FE(1)}$  Classification O : 70~140 Y : 120~240

